

EconoPIM™2 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 25\text{ A} / I_{CRM} = 50\text{ A}$
 - TRENCHSTOP™ IGBT7
 - Overload operation up to 175°C
 - Low $V_{CE,sat}$
- Mechanical features
 - High power density
 - Compact design
 - Al_2O_3 substrate with low thermal resistance
 - 2.5 kV AC 1 minute insulation



Typical appearance

Potential applications

- Auxiliary inverters
- Air conditioning
- Motor drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

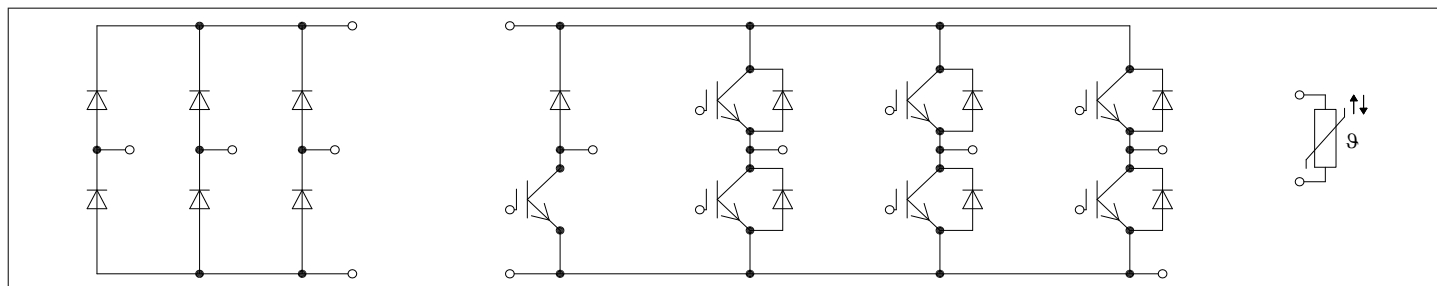


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			35		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25 \text{ °C}$, per switch		6.9		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$, per switch		5.9		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	3		5	Nm
Weight	G			180		g

Note: $T_{vj \text{ op}} > 150 \text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

The current under continuous operation is limited to 50 A rms per connector pin

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175 \text{ °C}$ $T_C = 120 \text{ °C}$	25	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$	50	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 25\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.60	1.85	V
			$T_{vj} = 125\ ^\circ C$	1.74		
			$T_{vj} = 175\ ^\circ C$	1.82		
Gate threshold voltage	V_{GEth}	$I_C = 0.525\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 600\ V$		0.395		µC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		4.77		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		0.017		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$		0.0056	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 9.1\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.040		µs
			$T_{vj} = 125\ ^\circ C$	0.042		
			$T_{vj} = 175\ ^\circ C$	0.043		
Rise time (inductive load)	t_r	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 9.1\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.045		µs
			$T_{vj} = 125\ ^\circ C$	0.048		
			$T_{vj} = 175\ ^\circ C$	0.050		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 9.1\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.209		µs
			$T_{vj} = 125\ ^\circ C$	0.325		
			$T_{vj} = 175\ ^\circ C$	0.376		
Fall time (inductive load)	t_f	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 9.1\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.164		µs
			$T_{vj} = 125\ ^\circ C$	0.233		
			$T_{vj} = 175\ ^\circ C$	0.300		
Turn-on energy loss per pulse	E_{on}	$I_C = 25\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 9.1\ \Omega, di/dt = 640\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	2.29		mJ
			$T_{vj} = 125\ ^\circ C$	3.01		
			$T_{vj} = 175\ ^\circ C$	3.52		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	$I_C = 25\text{ A}$, $V_{CC} = 600\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 9.1\text{ }\Omega$, $dv/dt = 2900\text{ V}/\mu\text{s}$ ($T_{vj} = 175\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1.57		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	2.58		
			$T_{vj} = 175\text{ }^\circ\text{C}$	3.15		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 800\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 8\text{ }\mu\text{s}$, $T_{vj} = 150\text{ }^\circ\text{C}$	80		A
			$t_p \leq 7\text{ }\mu\text{s}$, $T_{vj} = 175\text{ }^\circ\text{C}$	75		
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.967	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		0.170		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^\circ\text{C}$

Note: $T_{vj\text{ op}} > 150\text{ }^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ }^\circ\text{C}$	1200	V
Continuous DC forward current	I_F		25	A
Repetitive peak forward current	I_{FRM}	$t_p = 1\text{ ms}$	50	A
I^2t - value	I^2t	$t_p = 10\text{ ms}$, $V_R = 0\text{ V}$	$T_{vj} = 125\text{ }^\circ\text{C}$	A^2s
			$T_{vj} = 175\text{ }^\circ\text{C}$	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 25\text{ A}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	1.83	2.30	V
			$T_{vj} = 125\text{ }^\circ\text{C}$	1.70		
			$T_{vj} = 175\text{ }^\circ\text{C}$	1.63		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Peak reverse recovery current	I_{RM}	$V_{CC} = 600\text{ V}$, $I_F = 25\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 640\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	17.3		A
			$T_{vj} = 125\text{ °C}$	22.1		
			$T_{vj} = 175\text{ °C}$	25.1		
Recovered charge	Q_r	$V_{CC} = 600\text{ V}$, $I_F = 25\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 640\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	2.01		μC
			$T_{vj} = 125\text{ °C}$	3.57		
			$T_{vj} = 175\text{ °C}$	4.72		
Reverse recovery energy	E_{rec}	$V_{CC} = 600\text{ V}$, $I_F = 25\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 640\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	0.74		mJ
			$T_{vj} = 125\text{ °C}$	1.36		
			$T_{vj} = 175\text{ °C}$	1.79		
Thermal resistance, junction to case	R_{thJC}	per diode			1.43	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		0.182		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	1600	V
Maximum RMS forward current per chip	I_{FRMSM}	$T_C = 80\text{ °C}$		70	A
Maximum RMS current at rectifier output	I_{RMSM}	$T_C = 80\text{ °C}$		100	A
Surge forward current	I_{FSM}	$t_P = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	560	A
			$T_{vj} = 150\text{ °C}$	435	
I^2t - value	I^2t	$t_P = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	1570	A^2s
			$T_{vj} = 150\text{ °C}$	945	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 25 \text{ A}$	$T_{vj} = 150 \text{ °C}$		0.88		V
Reverse current	I_r	$T_{vj} = 150 \text{ °C}, V_R = 1600 \text{ V}$			1		mA
Thermal resistance, junction to case	R_{thJC}	per diode				0.870	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W/(m·K)}$			0.166		K/W
Temperature under switching conditions	$T_{vj, op}$			-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175 \text{ °C}$	$T_C = 125 \text{ °C}$	15	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$		30	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE \text{ sat}}$	$I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ °C}$		1.60	1.85	V
			$T_{vj} = 125 \text{ °C}$		1.74		
			$T_{vj} = 175 \text{ °C}$		1.82		
Gate threshold voltage	V_{GEth}	$I_C = 0.553 \text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25 \text{ °C}$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15 \text{ V}, V_{CC} = 600 \text{ V}$			0.234		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25 \text{ °C}$			0		Ω
Input capacitance	C_{ies}	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$			2.82		nF
Reverse transfer capacitance	C_{res}	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$			0.01		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$			0.003	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}, T_{vj} = 25 \text{ °C}$				100	nA

(table continues...)

Table 10 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	t_{don}	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 10\ \Omega$	$T_{vj} = 25\text{ °C}$	0.034		μs
			$T_{vj} = 125\text{ °C}$	0.035		
			$T_{vj} = 175\text{ °C}$	0.036		
Rise time (inductive load)	t_r	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 10\ \Omega$	$T_{vj} = 25\text{ °C}$	0.053		μs
			$T_{vj} = 125\text{ °C}$	0.054		
			$T_{vj} = 175\text{ °C}$	0.055		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 10\ \Omega$	$T_{vj} = 25\text{ °C}$	0.336		μs
			$T_{vj} = 125\text{ °C}$	0.534		
			$T_{vj} = 175\text{ °C}$	0.632		
Fall time (inductive load)	t_f	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 10\ \Omega$	$T_{vj} = 25\text{ °C}$	0.272		μs
			$T_{vj} = 125\text{ °C}$	0.313		
			$T_{vj} = 175\text{ °C}$	0.333		
Turn-on energy loss per pulse	E_{on}	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 10\ \Omega$, $di/dt = 520\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	4.57		mJ
			$T_{vj} = 125\text{ °C}$	5.55		
			$T_{vj} = 175\text{ °C}$	6.07		
Turn-off energy loss per pulse	E_{off}	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 10\ \Omega$, $dv/dt = 2100\text{ V}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	0.927		mJ
			$T_{vj} = 125\text{ °C}$	1.49		
			$T_{vj} = 175\text{ °C}$	1.77		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 800\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 8\ \mu\text{s}$, $T_{vj} = 150\text{ °C}$	48		A
			$t_p \leq 7\ \mu\text{s}$, $T_{vj} = 175\text{ °C}$	45		
Thermal resistance, junction to case	R_{thJC}	per IGBT			1.29	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		0.180		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC forward current	I_F			10	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$		20	A
I^2t - value	I^2t	$t_P = 10\text{ ms}, V_R = 0\text{ V}$	$T_{vj} = 125\text{ °C}$	30	A^2s
			$T_{vj} = 175\text{ °C}$	25	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 10\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$	1.72	2.10	V
			$T_{vj} = 125\text{ °C}$	1.59		
			$T_{vj} = 175\text{ °C}$	1.52		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600\text{ V}, I_F = 10\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 450\text{ A}/\mu s (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	11.2		A
			$T_{vj} = 125\text{ °C}$	13.4		
			$T_{vj} = 175\text{ °C}$	14.5		
Recovered charge	Q_r	$V_{CC} = 600\text{ V}, I_F = 10\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 450\text{ A}/\mu s (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	0.95		μC
			$T_{vj} = 125\text{ °C}$	1.68		
			$T_{vj} = 175\text{ °C}$	2.05		
Reverse recovery energy	E_{rec}	$V_{CC} = 600\text{ V}, I_F = 10\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 450\text{ A}/\mu s (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	0.37		mJ
			$T_{vj} = 125\text{ °C}$	0.66		
			$T_{vj} = 175\text{ °C}$	0.83		
Thermal resistance, junction to case	R_{thJC}	per diode			1.81	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(m \cdot K)$		0.181		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}, R_{100} = 493\text{ Ω}$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

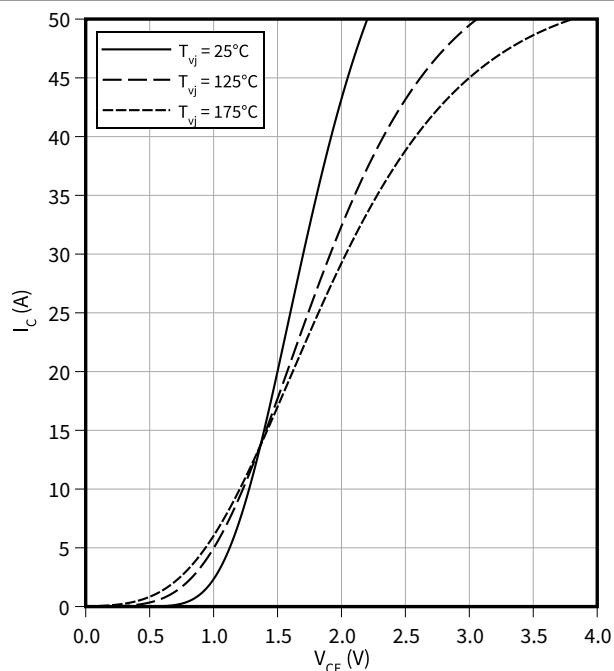
Note: Specification according to the valid application note.

8 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

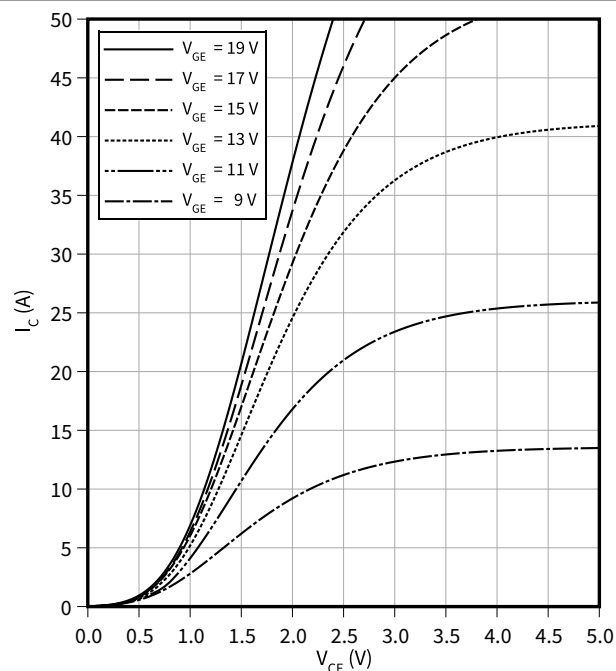
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

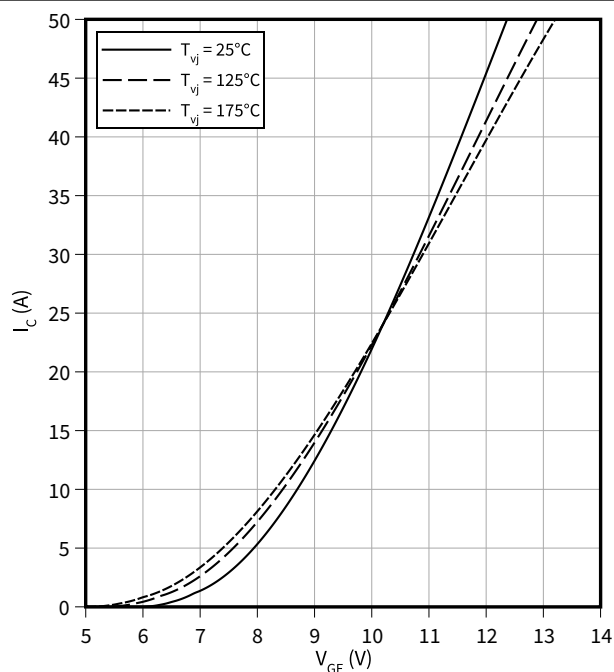
$$T_{vj} = 175^\circ\text{C}$$



Transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

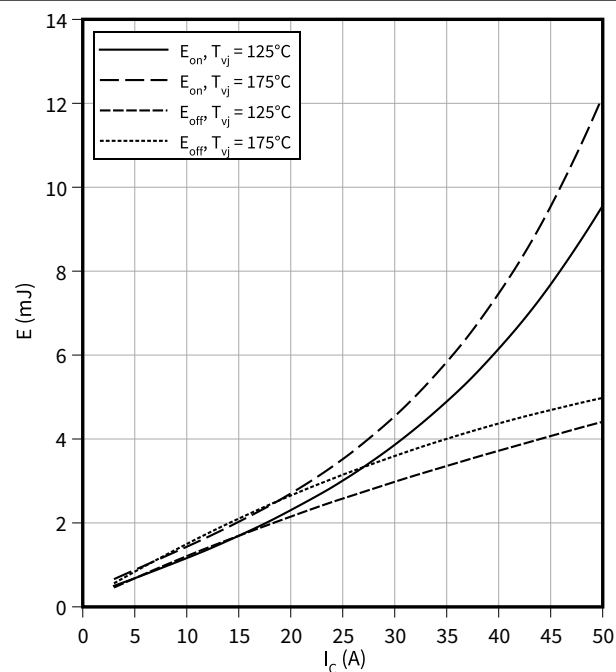
$$V_{CE} = 20 \text{ V}$$



Switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

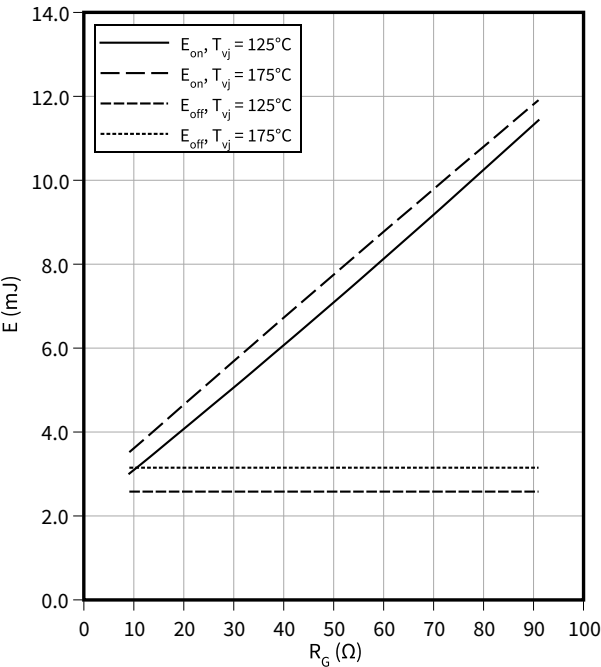
$$R_{Goff} = 9.1 \Omega, R_{Gon} = 9.1 \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} = 600 \text{ V}$$



8 Characteristics diagrams

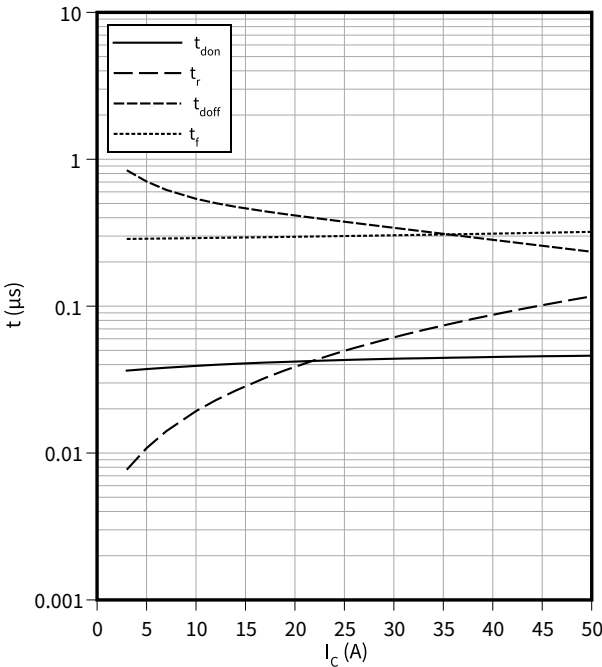
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 25\text{ A}$, $V_{CC} = 600\text{ V}$



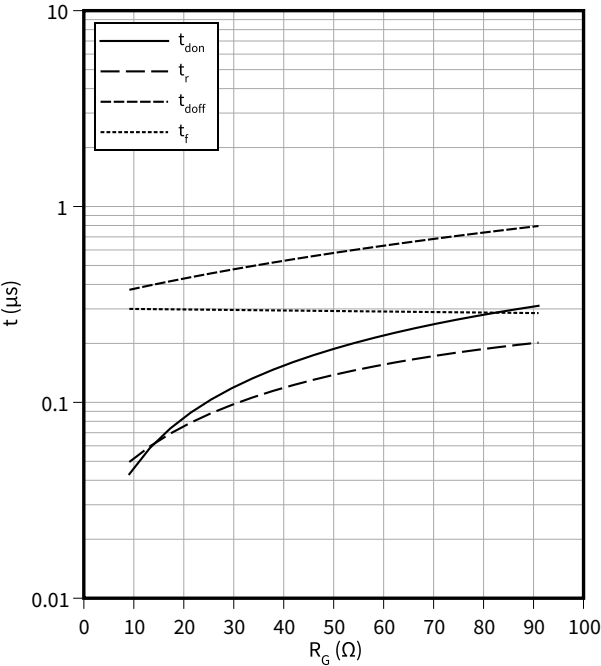
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 9.1\ \Omega$, $R_{Gon} = 9.1\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $V_{CC} = 600\text{ V}$, $T_{vj} = 175\text{ °C}$



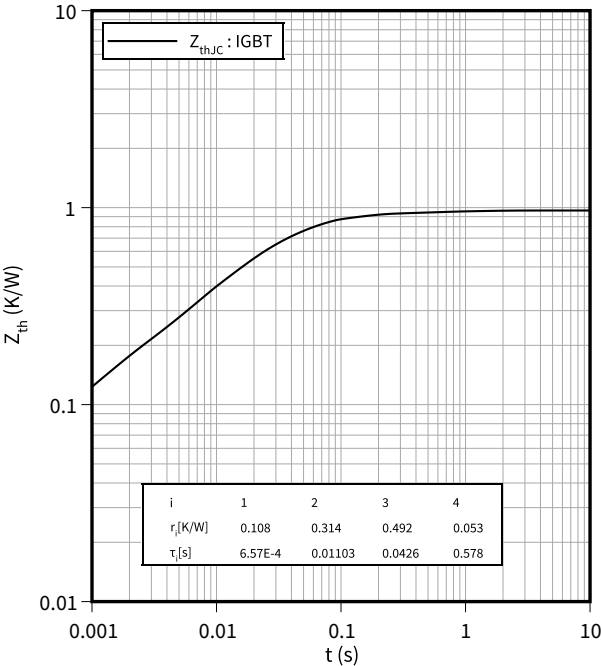
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 25\text{ A}$, $V_{CC} = 600\text{ V}$, $T_{vj} = 175\text{ °C}$



Transient thermal impedance , IGBT, Inverter

$Z_{th} = f(t)$



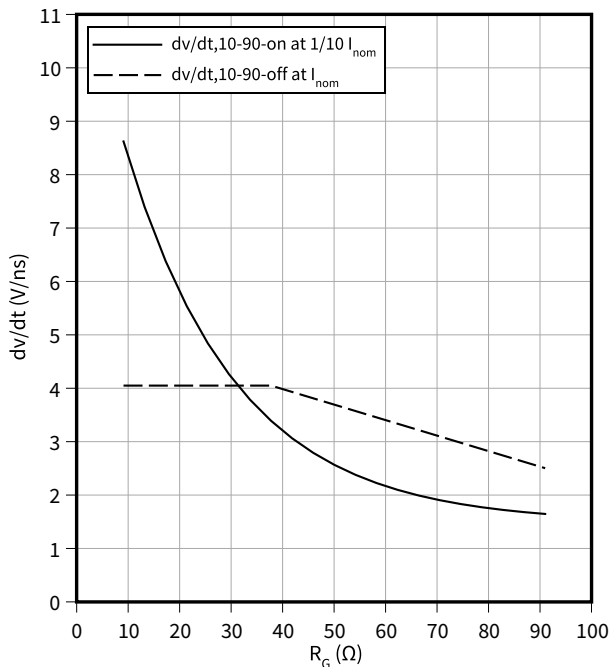
i	1	2	3	4
r_i [K/W]	0.108	0.314	0.492	0.053
τ_i [s]	6.57E-4	0.01103	0.0426	0.578

8 Characteristics diagrams

Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$

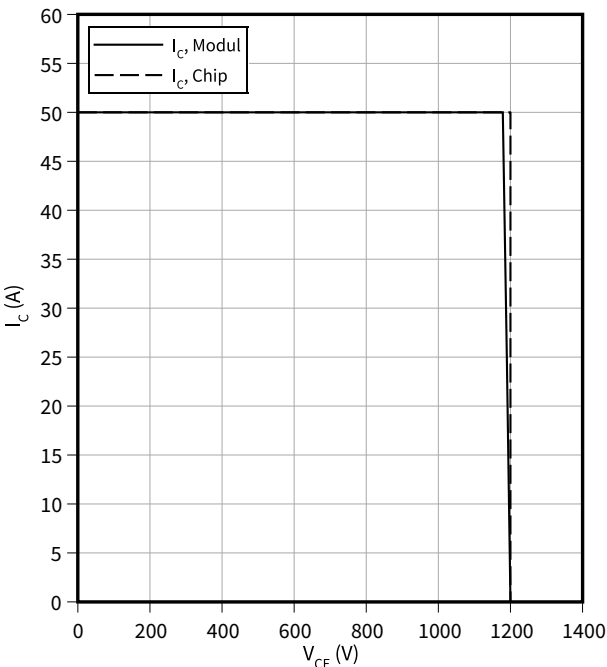
$I_C = 25\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 25\text{ }^\circ\text{C}$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

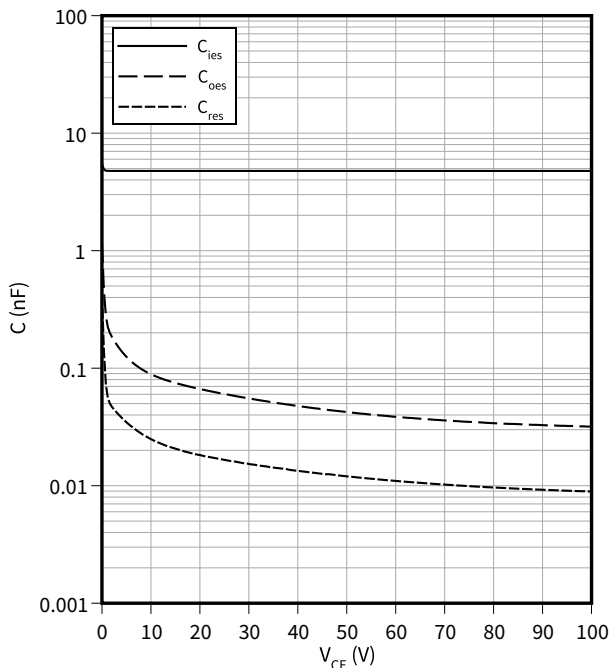
$R_{Goff} = 9.1\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$



Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

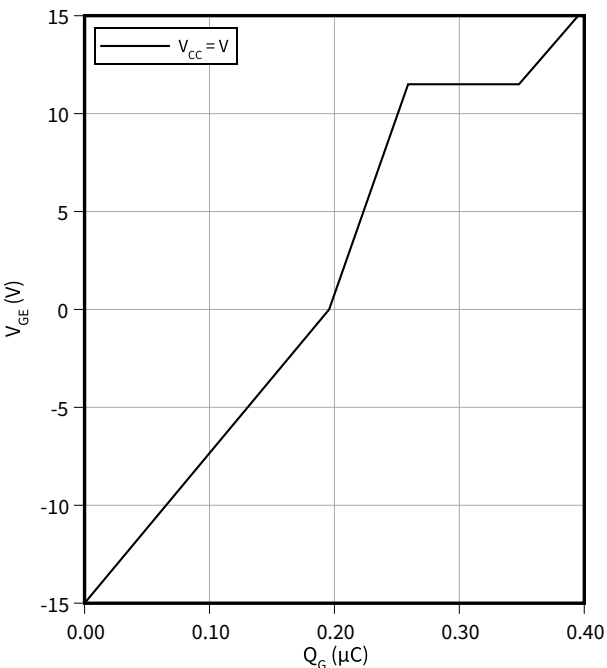
$f = 100\text{ kHz}$, $V_{GE} = 0\text{ V}$, $T_{vj} = 25\text{ }^\circ\text{C}$



Gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$

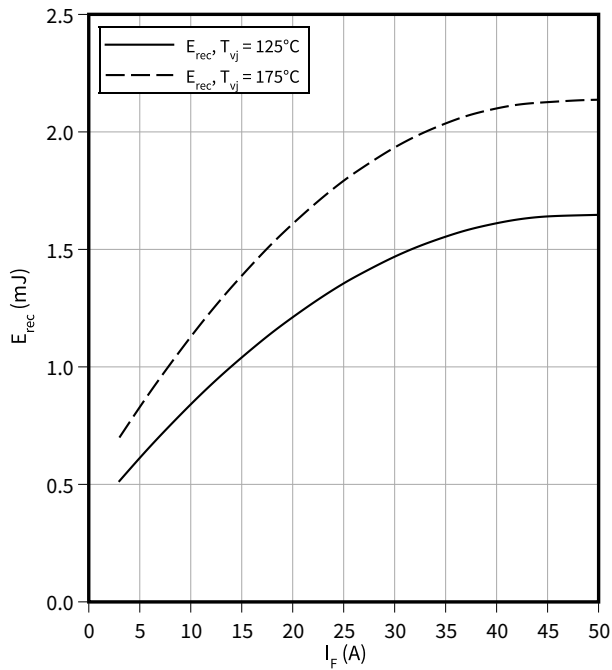
$I_C = 25\text{ A}$, $T_{vj} = 25\text{ }^\circ\text{C}$



8 Characteristics diagrams

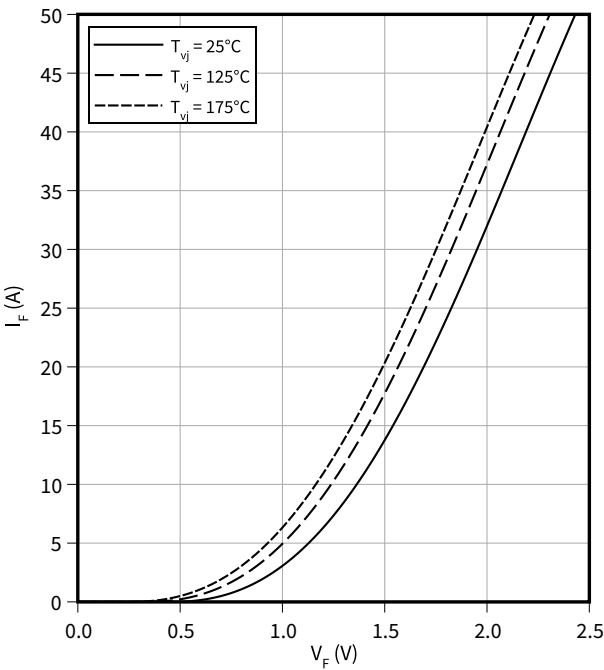
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = 9.1, V_{CC} = 600\text{ V}$



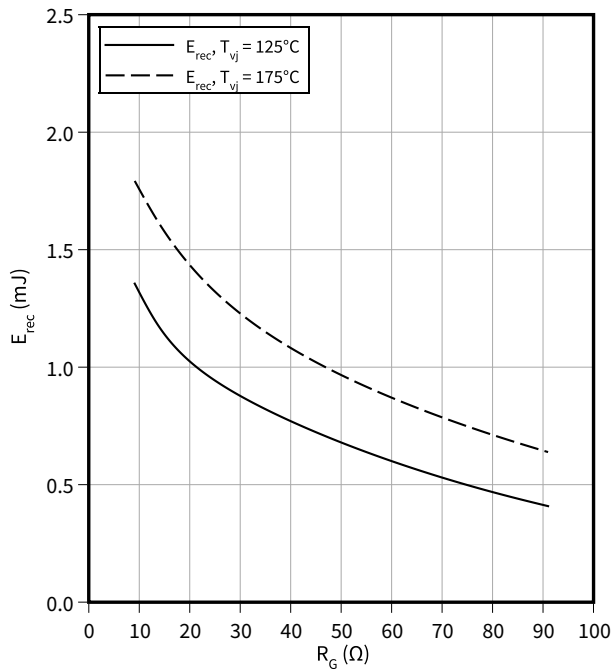
Forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$



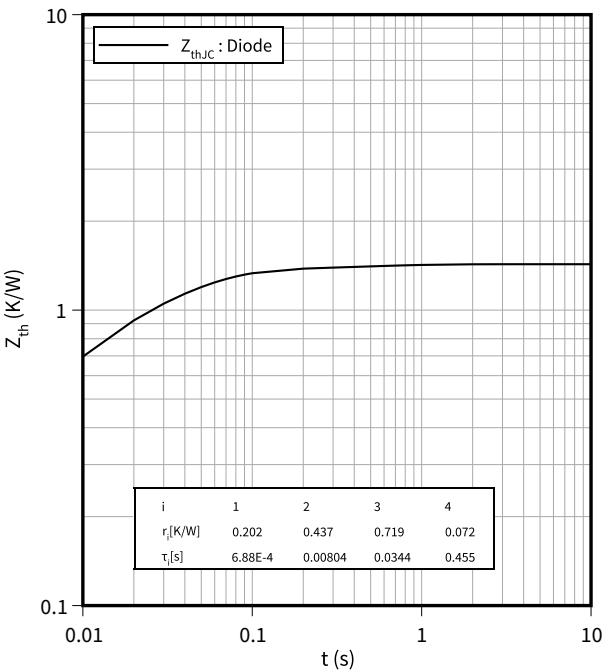
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 25\text{ A}, V_{CC} = 600\text{ V}$



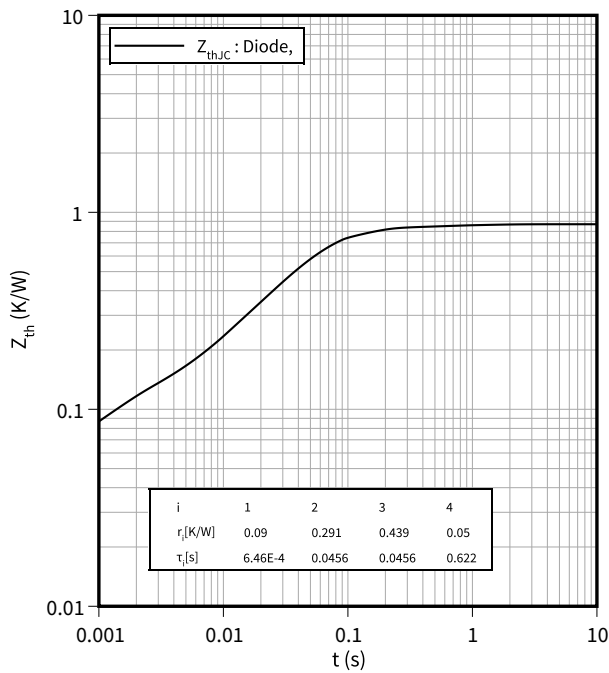
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



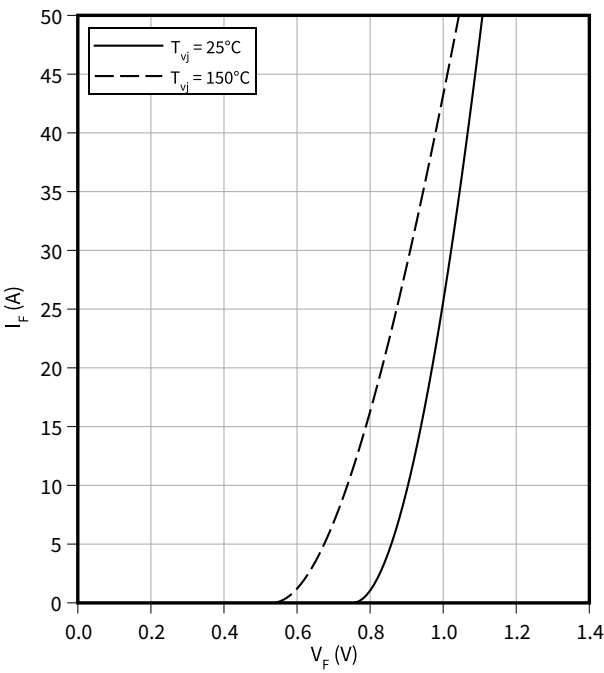
Transient thermal impedance, Diode, Rectifier

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Rectifier

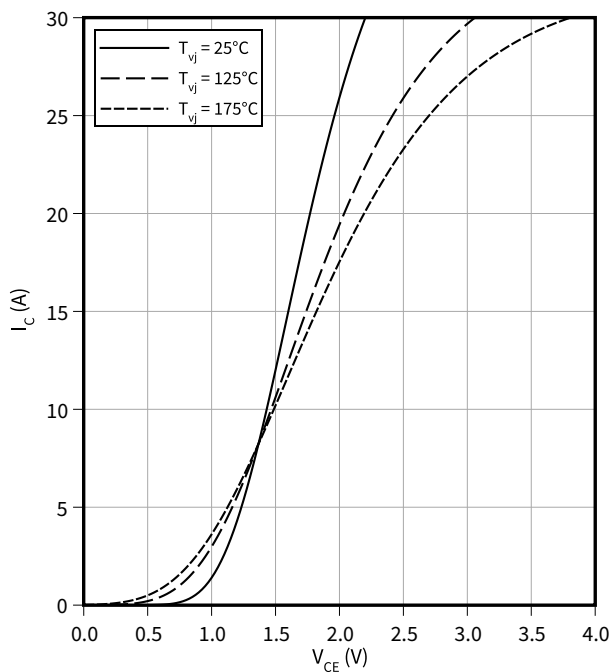
$I_F = f(V_F)$



Output characteristic (typical), IGBT, Brake-Chopper

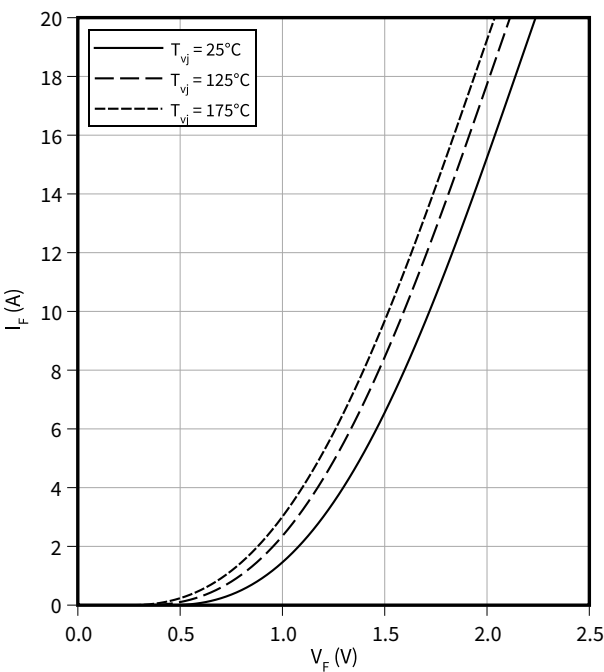
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



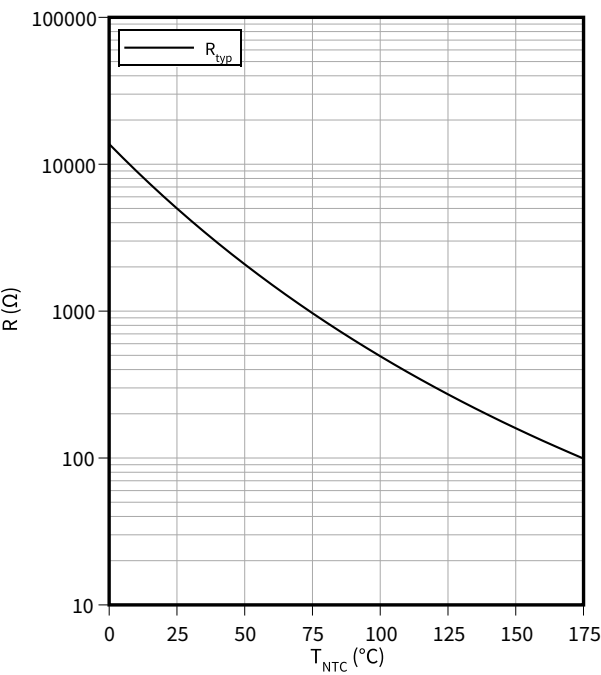
Forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 **Circuit diagram**

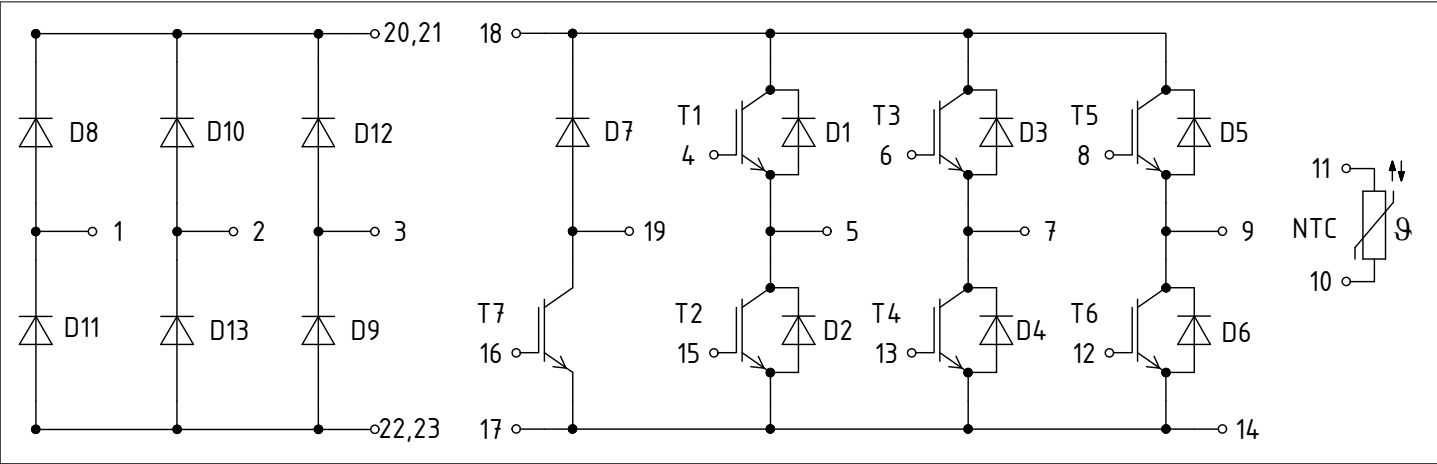
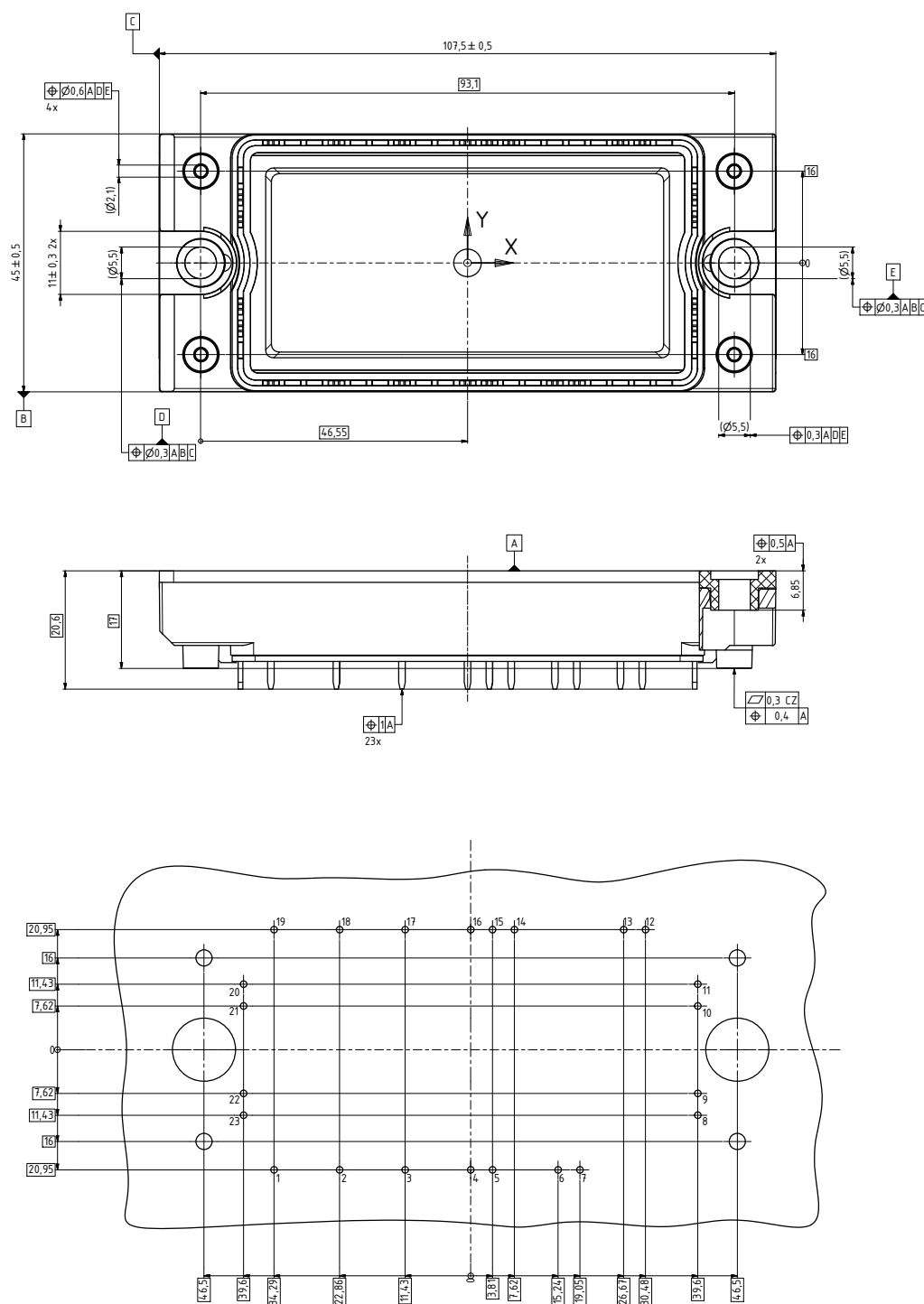


Figure 1

10 Package outlines



For PressFIT pin: Details about hole specification for contacts refer to AN2007-09
For Solderpin: Details about hole specification for contacts refer to AN2017-03

Recommended tolerance of threaded holes in heatsink ± 0,1 mm.
Dimensions according to ISO 14405 (G5) (Method of least squares (LSQ)).
Reference D and E defined with (G5)
ISO 8015 - Independency principle

W00213332.00

Figure 2

11 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example			
			
71549142846550549911530		71549142846550549911530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-11-14	Target datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2022-11-28	Final datasheet

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